TOSHIBA

RN2101F~RN2106F

TOSHIBA TRANSISTOR SILICON PNP EPITAXIAL TYPE (PCT PROCESS)

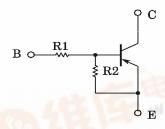
RN2101F, RN2102F, RN2103F RN2104F, RN2105F, RN2106F

SWITCHING, INVERTER CIRCUIT, INTERFACE CIRCUIT

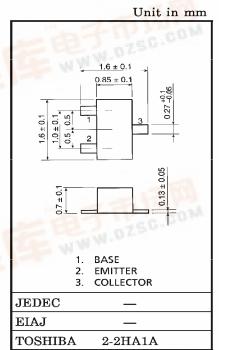
AND DRIVER CIRCUIT APPLICATIONS.

- With Built-in Bias Resistors
- Simplify Circuit Design
- Reduce a Quantity of Parts and Manufacturing Process
- Complementary to RN1101F~RN1106F

EQUIVALENT CIRCUIT AND BIAS RESISTOR VALUES



TYPE No.	R1 (kΩ)	R2 (kΩ)
RN2101F	4.7	4.7
RN2102F	10	10
RN2103F	22	22
RN2104F	47	47
RN2105F	2.2	47
RN2106F	4.7	47



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MAXIMUM RATINGS ($Ta = 25^{\circ}C$)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage	DNO101E 0100E	VCBO	-50	V
Collector-Emitter Voltage	RN2101F~2106F	VCEO	-50	V
Emitter-Base Voltage	RN2101F~2104F		-10	V
	RN2105F, 2106F	$V_{ m EBO}$	-5	
Collector Current		$I_{\mathbf{C}}$	-100	mA
Collector Power Dissipation	RN2101F~2106F	$P_{\mathbf{C}}$	100	mW
Junction Temperature	RN2101F~2106F	$T_{ m j}$	150	°C
Storage Temperature Range		${f T}_{ m stg}$	-55~150	°C
			LAR C	

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TOSHIBA is continually working to improve the quality and the reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to observe standards of safety, and to avoid situations in which a malfunction or failure of a TOSHIBA product could cause loss of human life, bodily injury or damage to property. In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent products specifications. Also, please keep in mind the precautions and conditions set forth in the TOSHIBA Semiconductor Reliability Handbook.

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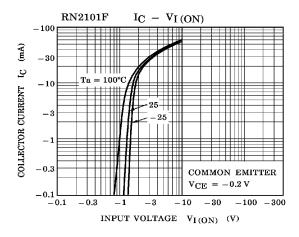
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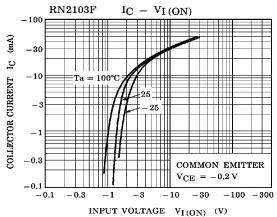
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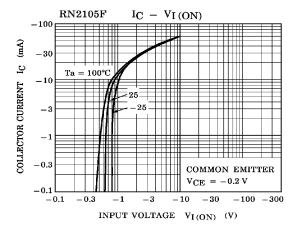


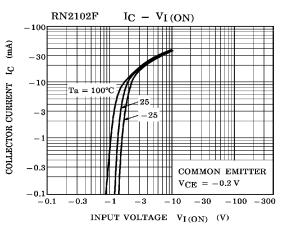
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

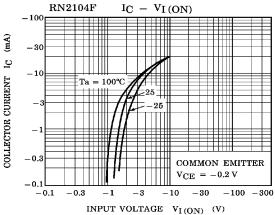
CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off	RN2101F~	ICBO	$V_{CB} = -50 \text{ V}, I_{E} = 0$	_	_	-100	A
Current	2106F	I_{CEO}	$V_{CE} = -50 \text{ V}, I_{B} = 0$	_		-500	nA
Emitter Cut-off Current	RN2101F		$V_{EB} = -10 \text{ V}, I_{C} = 0$	-0.82	_	-1.52	mA
	RN2102F			-0.38	_	-0.71	
	RN2103F			-0.17	_	-0.33	
	RN2104F			-0.082	_	-0.15	
	RN2105F			-0.078	_	-0.145	
	RN2106F		$V_{EB} = -5 V, I_C = 0$	-0.074	_	-0.138	
	RN2101F			30	_	_	
	RN2102F			50			
	RN2103F		$V_{CE} = -5 V$	70	_		
DC Current Gain	RN2104F	$\mathbf{h_{FE}}$	$I_{\rm C} = -10\mathrm{mA}$	80	_		
	RN2105F			80		_	
	RN2106F			80			
Collector-Emitter	RN2101F~		$I_{\rm C} = -5 \rm mA$				
Saturation Voltage	2106F	V _{CE} (sat)	$I_{\rm B} = -0.25 \mathrm{mA}$	-	-0.1	-0.3	V
8	RN2101F		-Б	-1.1		-2.0	
	RN2102F		$V_{CE} = -0.2 V$ $I_{C} = -5 \text{mA}$	-1.2		-2.4	V
	RN2103F	V _I (ON)		-1.3		-3.0	
Input Voltage (ON)	RN2104F			-1.5		-5.0	
	RN2105F			-0.6		-1.1	
	RN2106F			-0.7		-1.3	
	RN2101F~			-0.1		1.0	
Input Voltage (OFF)	2104F		$V_{ ext{CE}} = -5 \text{ V}$ $I_{ ext{C}} = -0.1 \text{ mA}$	-1.0	_	-1.5	v
	RN2105F,						
	2106F			-0.5	_	-0.8	
	RN2101F~		$V_{CE} = -10 \text{ V},$				
Transition Frequency	2106F	${f f_T}$	$I_{\rm C} = -5 \mathrm{mA}$	-	200	_	MHz
Collector Output	RN2101F~	С.	$V_{CB} = -10 \text{ V}, I_{E} = 0$		3	6	~ Tr
Capacitance	2106F	$\mathrm{C_{ob}}$	f = 1 MHz	_	3	0	рF
Input Resistor	RN2101F	R1		3.29	4.7	6.11	
	RN2102F			7	10	13	
	RN2103F			15.4	22	28.6	1.0
	RN2104F			32.9	47	61.1	$\mathbf{k}\Omega$
	RN2105F			1.54	2.2	2.86	
	RN2106F			3.29	4.7	6.11	
Resistor Ratio	RN2101F~	R1 / R2		0.0	1.0		
	2104F			0.9	1.0	1.1	
	RN2105F			0.0421	0.0468	0.0515	
	RN2106F			0.09	0.1	0.11	

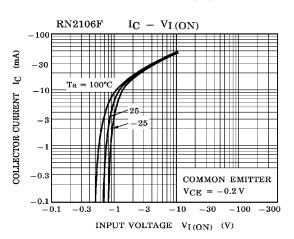


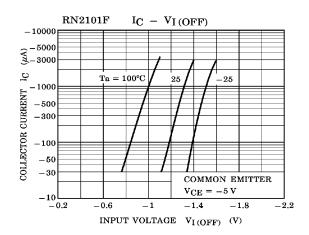


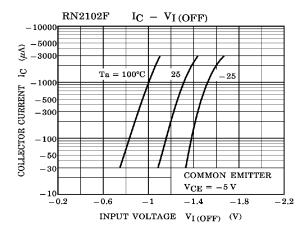


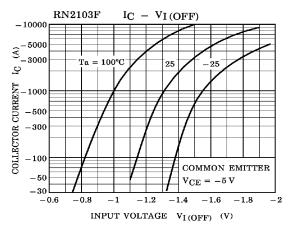


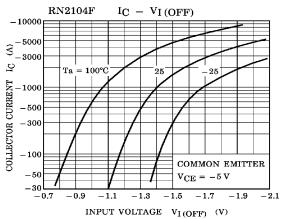


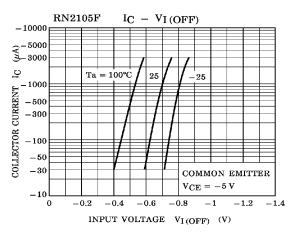


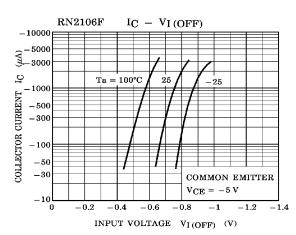


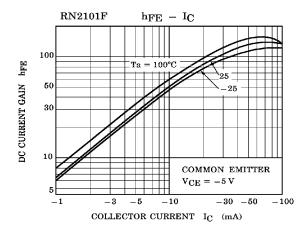


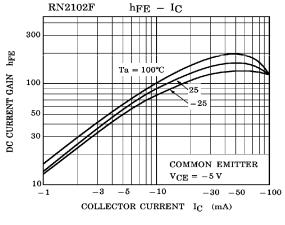


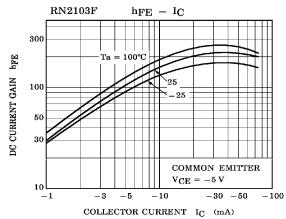


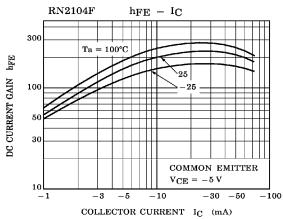


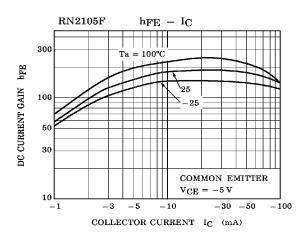


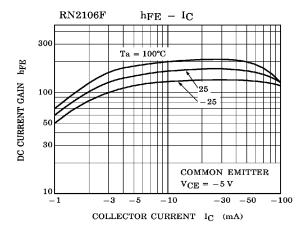


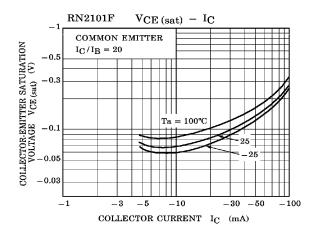


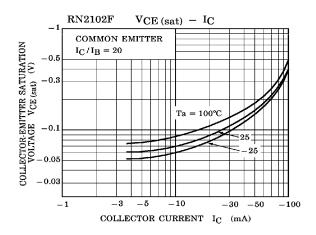


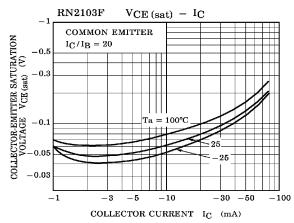


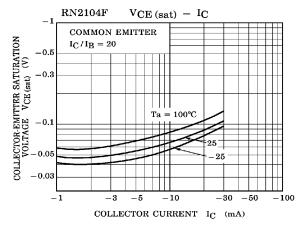


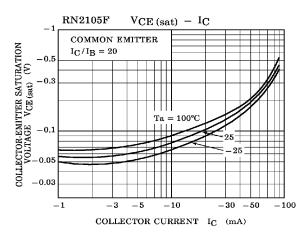


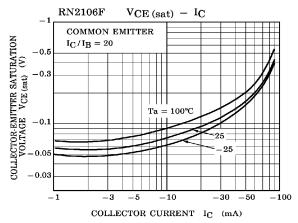












TYPE NAME	MARKING		
RN2101F	Type Name Y A		
RN2102F	Type Name Y B		
RN2103F	Type Name Y C		
RN2104F	Type Name Y D		
RN2105F	Type Name Y E		
RN2106F	Type Name Y F		